

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ max	I_D $T_A = +25^\circ\text{C}$
12V	0.15Ω @ $V_{GS} = 4.5\text{V}$	1.41A
	0.185Ω @ $V_{GS} = 2.5\text{V}$	1.25A
	0.21Ω @ $V_{GS} = 1.8\text{V}$	1.16A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power management functions

Features

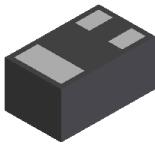
- Low On-Resistance
- Very Low Gate Threshold Voltage $V_{GS(\text{TH})}$, 1.0V max
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

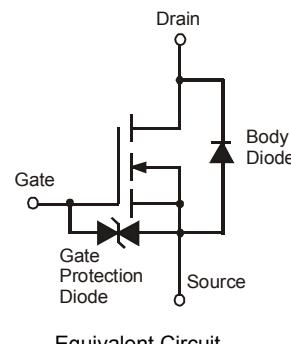
- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208 ^(e4)
- Weight: 0.001 grams (approximate)



X1-DFN1006-3



Bottom View

Top View
Internal Schematic

Equivalent Circuit

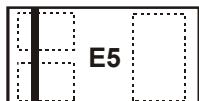
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN1150UFB-7B	X1-DFN1006-3	10,000/Tape & Reel

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



Top View

E5 = Product Type Marking Code
Bar Denotes Gate and Source Side

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	12	V
Gate-Source Voltage			V_{GSS}	± 6	V
Continuous Drain Current (Note 5) $V_{GS} = 4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	1.41 1.15	A
Pulsed Drain Current (10 μs pulse, duty cycle = 1%)			I_{DM}	7	A
Maximum Body Diode continuous Current			I_S	1	A

 Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	$T_A = +25^\circ\text{C}$	P_D	0.5	W
	$T_A = +70^\circ\text{C}$		0.3	
Thermal Resistance, Junction to Ambient (Note 5)		Steady state	$R_{\theta JA}$	251
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

 Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	12	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{DSS}	—	—	100	nA	$V_{DS} = 12\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 1	μA	$V_{GS} = \pm 6\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	0.35	—	1.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(\text{ON})}$	—	—	150	$\text{m}\Omega$	$V_{GS} = 4.5\text{V}, I_D = 1\text{A}$
			—	185		$V_{GS} = 2.5\text{V}, I_D = 1\text{A}$
			—	210		$V_{GS} = 1.8\text{V}, I_D = 1\text{A}$
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	$V_{GS} = 0\text{V}, I_S = 150\text{mA}$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	106	—	pF	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	23	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	21	—	pF	
Gate resistance	R_g	—	92.4	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	1.5	—	nC	$V_{DS} = 4\text{V}, I_D = 1\text{A}$
Gate-Source Charge	Q_{qs}	—	0.2	—	nC	
Gate-Drain Charge	Q_{qd}	—	0.2	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	4.1	—	ns	$V_{DD} = 4\text{V}, V_{GS} = 6\text{V}, I_D = 1\text{A}$ $R_G = 1\Omega$
Turn-On Rise Time	t_r	—	34.5	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	57	—	ns	
Turn-Off Fall Time	t_f	—	30	—	ns	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Short duration pulse test used to minimize self-heating effect.

7. Guaranteed by design. Not subject to product testing.

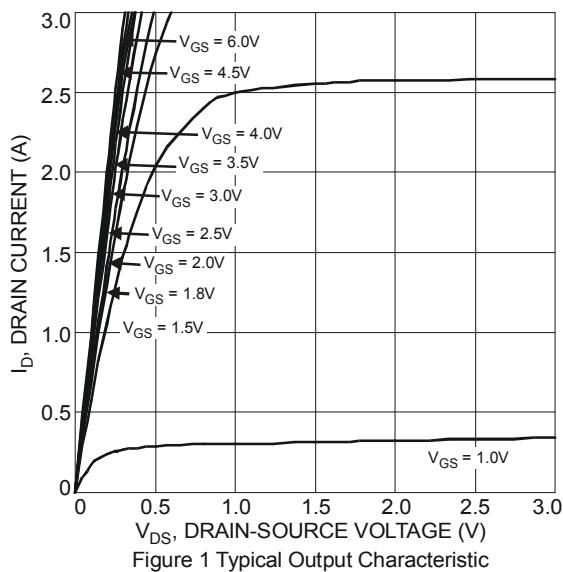


Figure 1 Typical Output Characteristic

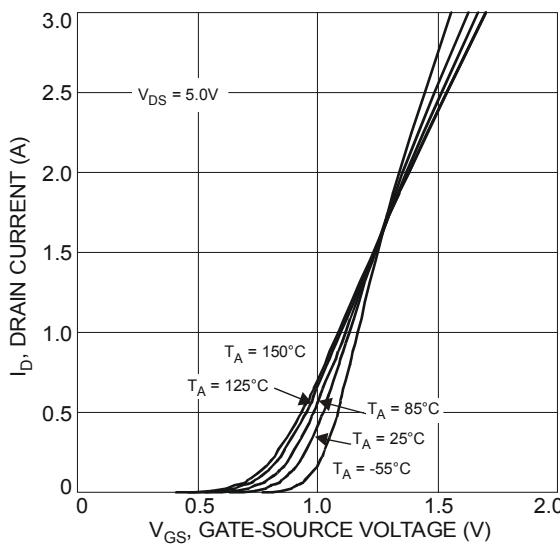


Figure 2 Typical Transfer Characteristics

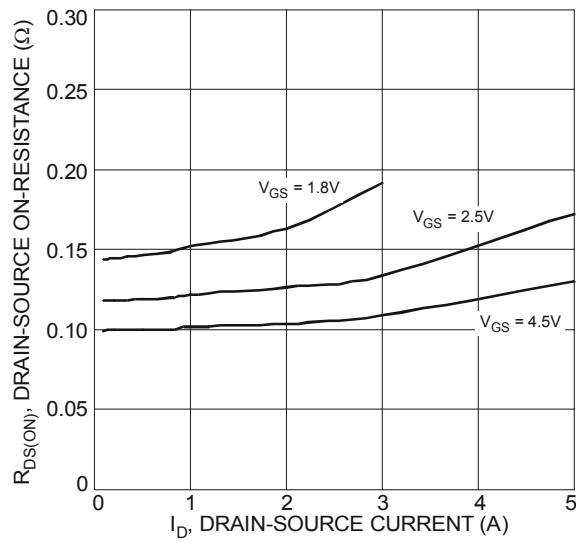


Figure 3 Typical On-Resistance vs.
Drain Current and Gate Voltage

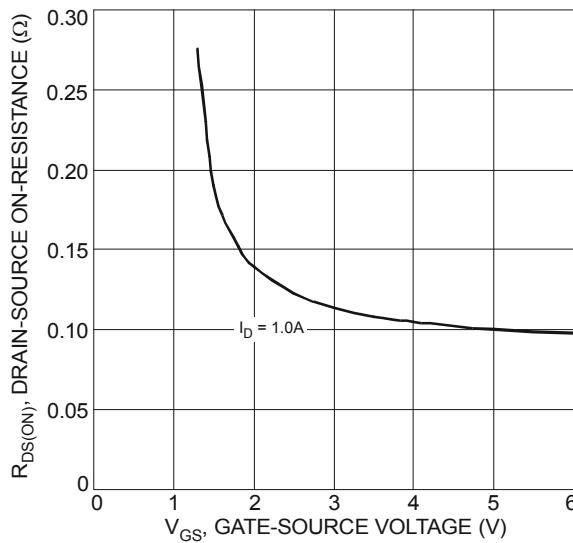


Figure 4 Typical Drain-Source On-Resistance
vs. Gate-Source Voltage

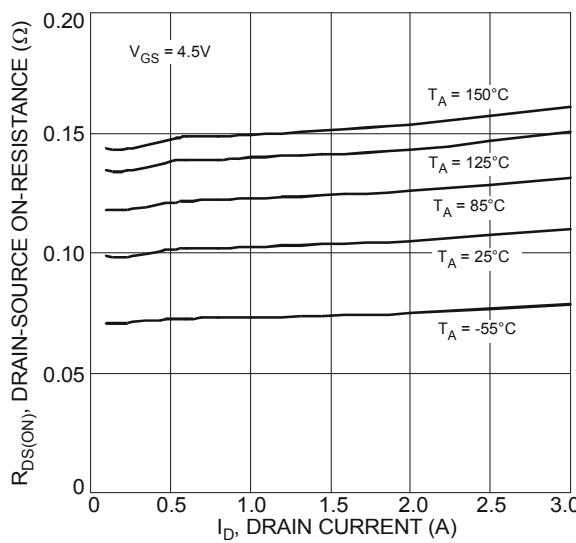


Figure 5 Typical On-Resistance vs.
Drain Current and Temperature

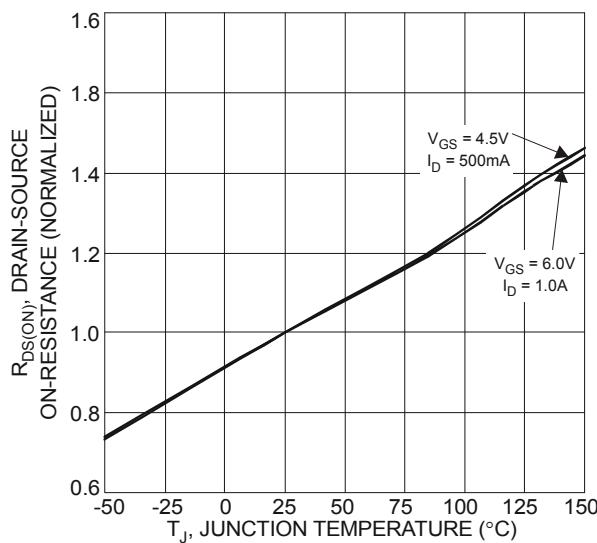
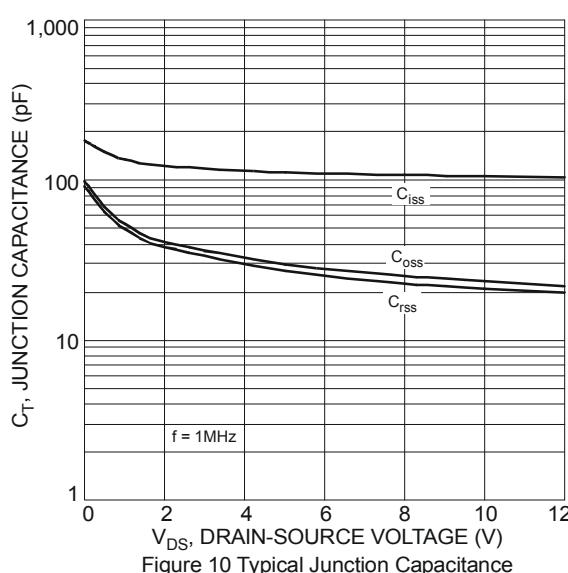
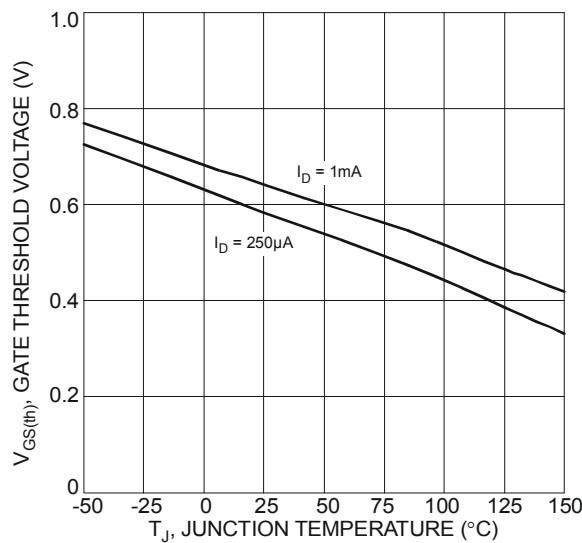
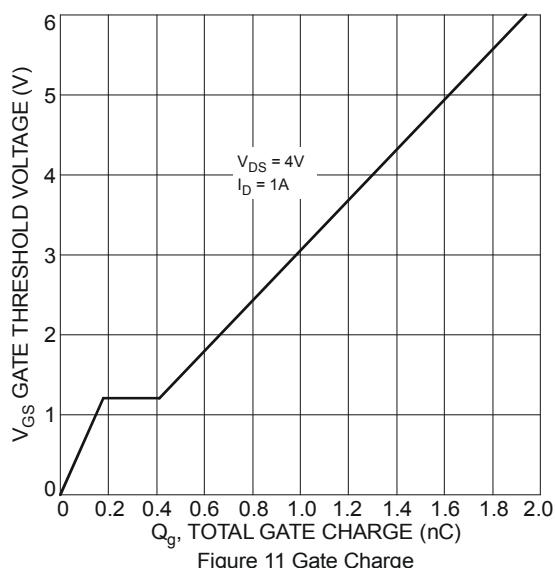
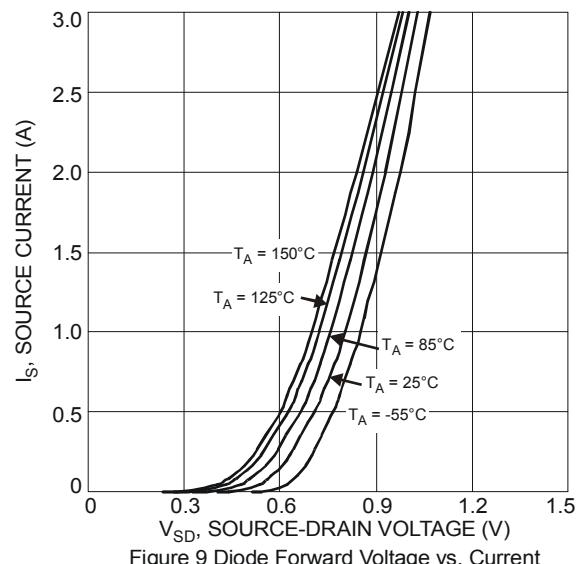
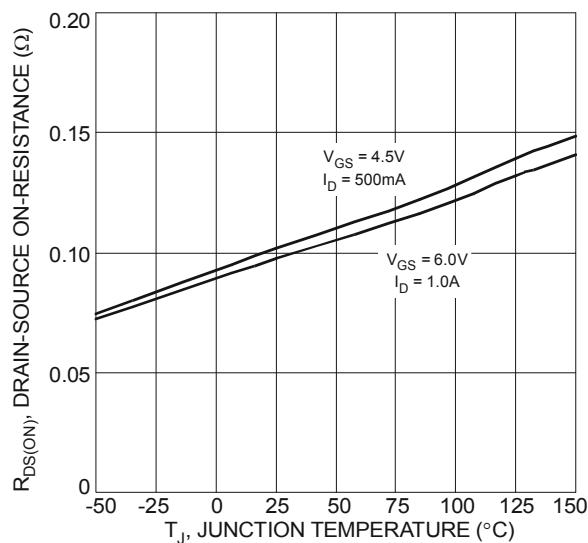
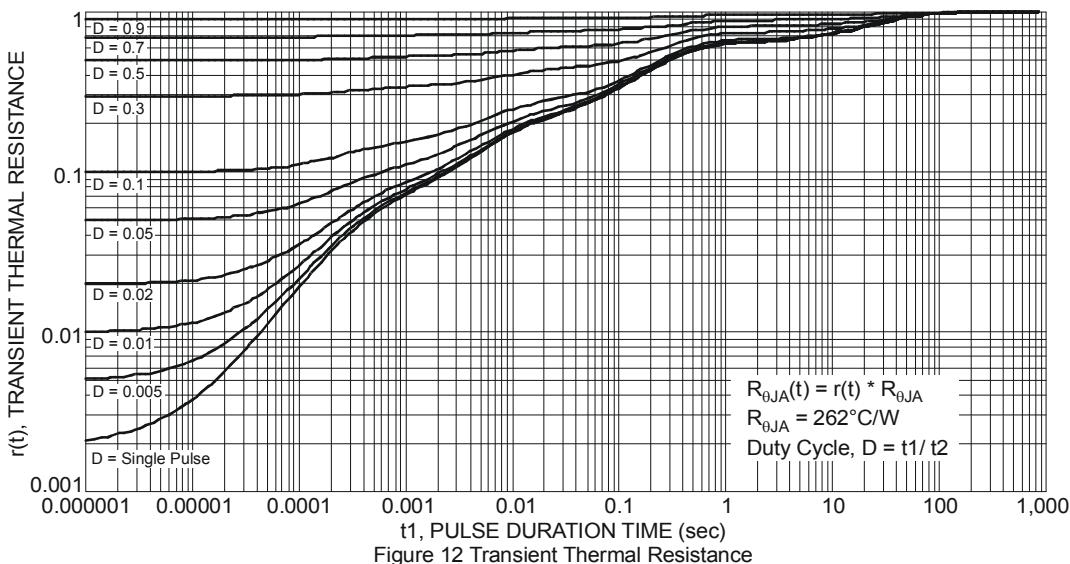


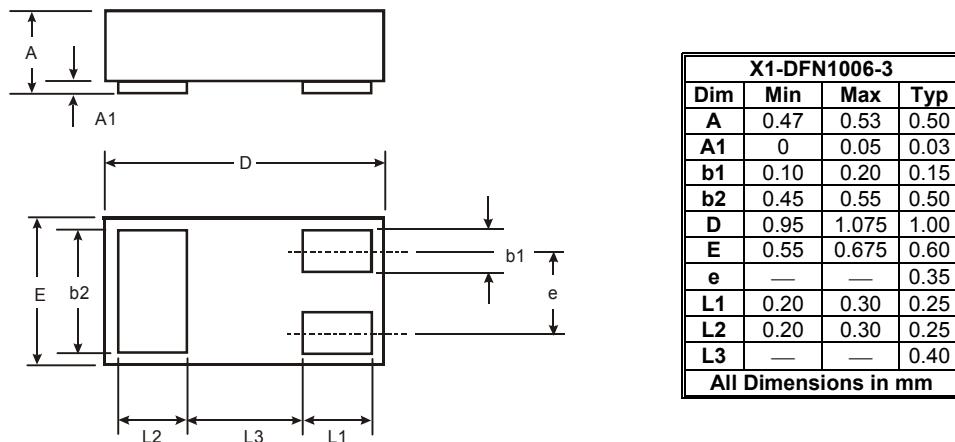
Figure 6 On-Resistance Variation with Temperature





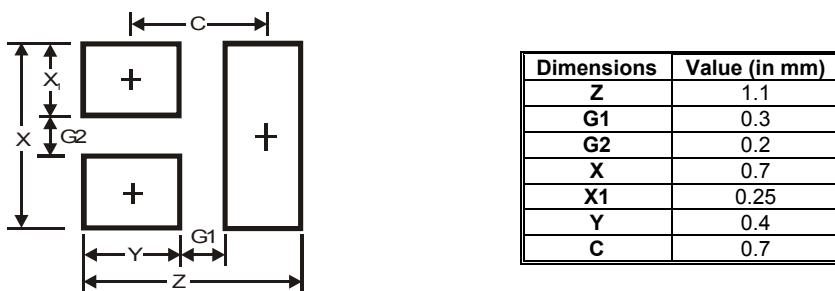
Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



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